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(54) **APPARATUSES INCLUDING SHALLOW TRENCH ISOLATION AND METHODS FOR FORMING SAME**

(71) Applicant: **MICRON TECHNOLOGY, INC.,**
BOISE, ID (US)

(72) Inventors: **Maxtheodore Tateno**, Higashihiroshima (JP); **Takashi Sasaki**, Higashihiroshima (JP)

(73) Assignee: **MICRON TECHNOLOGY, INC.,**
BOISE, ID (US)

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ABSTRACT

A semiconductor structure includes a trench in a substrate, one or more spacers at a bottom surface of the trench, and spin-on dielectric in the trench.

